# Non-Inverting 3-State Buffer, TTL Level

# **LSTTL-Compatible Inputs**

The NLU1GT125 MiniGate<sup>™</sup> is an advanced CMOS high-speed non-inverting buffer in ultra-small footprint.

The NLU1GT125 requires the 3-state control input  $\overline{OE}$  to be set High to place the output in the high impedance state.

The device input is compatible with TTL-type input thresholds and the output has a full 5.0 V CMOS level output swing.

The NLU1GT125 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

# **Features**

- High Speed:  $t_{PD} = 3.8 \text{ ns}$  (Typ) @  $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- TTL-Compatible Input:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2.0 \text{ V}$
- CMOS-Compatible Output:
  - $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @ Load
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Ultra-Small Packages
- These are Pb-Free Devices

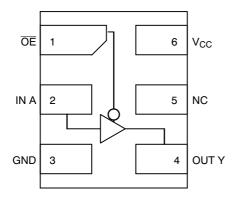


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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# MARKING DIAGRAMS



UDFN6 MU SUFFIX CASE 517AA





ULLGA6 1.0 x 1.0 CASE 613AD





ULLGA6 1.2 x 1.0 CASE 613AE





ULLGA6 1.45 x 1.0 CASE 613AF



7 = Device Marking M = Date Code

#### **PIN ASSIGNMENT**

1	ŌĒ			
2	IN A			
3	GND			
4	OUT Y			
5	NC			
6	V <sub>CC</sub>			

# **FUNCTION TABLE**

Input		Output
Α	ŌĒ	Υ
L	L	L
Н	L	Н
X	Н	Z

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V	
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC Input Diode Current V <sub>IN</sub> <	GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current V <sub>OUT</sub> <	GND	±20	mA
ΙO	DC Output Source/Sink Current		±12.5	mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin		±25	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin	±25	mA	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias	150	°C	
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating Oxygen Index: 28	to 34	UL 94 V-0 @ 0.125 in	
I <sub>LATCHUP</sub>	Latchup Performance Above V <sub>CC</sub> and Below GND at 125°C (Note	±500	mA	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

2. Tested to EIA / JESD78.

# **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter			Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	Digital Input Voltage		0	5.5	V
V <sub>OUT</sub>	Output Voltage			5.5	V
T <sub>A</sub>	Operating Free-Air Temperature			+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $ \begin{array}{c} V_{CC} = 3.3 \ V \pm 0.3 \ V \\ V_{CC} = 5.0 \ V \pm 0.5 \ V \\ \end{array} $		0 0	100 20	ns/V

# DC ELECTRICAL CHARACTERISTICS

				Т	A = 25 °	°C	<b>T</b> <sub>A</sub> = ·	+85°C	T <sub>A</sub> = - to +1	-55°C 25°C	
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Low-Level Input Voltage		3.0 4.5 to 5.5	1.4 2.0			1.4 2.0		1.4 2.0		V
V <sub>IL</sub>	Low-Level Input Voltage		3.0 4.5 to 5.5			0.53 0.8		0.53 0.8		0.53 0.8	V
V <sub>OH</sub>	High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	3.0 4.5		0 0	0.1 0.1		0.1 0.1		0.1 0.1	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Input Leakage Current	$0 \le V_{IN} \le 5.5 V$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$0 \le V_{IN} \le V_{CC}$	5.5			1.0		20		40	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	V <sub>IN</sub> = 3.4 V Other Input: V <sub>CC</sub> or GND	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μΑ
I <sub>OZ</sub>	3-State Leakage Current	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	0.0			±0.25		±2.5		±2.5	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

		V <sub>CC</sub>	Test	Т	A = 25 °	°C	T <sub>A</sub> =	+85°C		-55°C  25°C	
Symbol	Parameter	(V)	Condition	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, A to <b>Y</b> (Figures 3 and 5)	3.0 to 3.6	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
		4.5 to 5.5	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time, $\overline{OE}$ to Y (Figures 4 and 6)	3.0 to 3.6	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
		4.5 to 5.5	$C_L = 15 pF$ $C_L = 50 pF$		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time, $\overline{OE}$ to Y (Figures 4 and 6)	3.0 to 3.6	$C_L = 15 pF$ $C_L = 50 pF$		6.5 8.0	9.7 13.2	1.0 1.0	11.5 15.0		14.5 18.5	ns
		4.5 to 5.5	$C_L = 15 pF$ $C_L = 50 pF$		4.8 7.0	6.8 8.8	1.0 1.0	8.0 10.0		10.0 12.0	
C <sub>IN</sub>	Input Capacitance				4	10		10		10.0	pF
C <sub>OUT</sub>	3-State Output Capacitance (Output in High Impedance State)				6						pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 3)	5.0			14						pF

<sup>3.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}$ . C<sub>PD</sub> is used to determine the no-load dynamic power consumption:  $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$ .

# **SWITCHING WAVEFORMS**

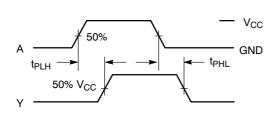
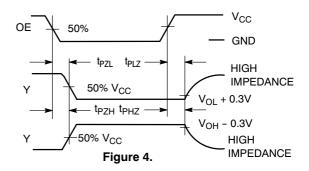
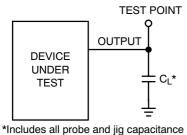
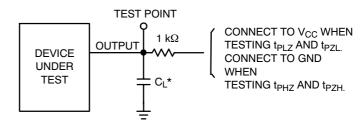


Figure 3. Switching Waveforms









\*Includes all probe and jig capacitance

**Figure 5. Test Circuit** 

Figure 6. Test Circuit

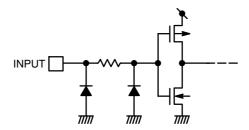


Figure 7. Input Equivalent Circuit

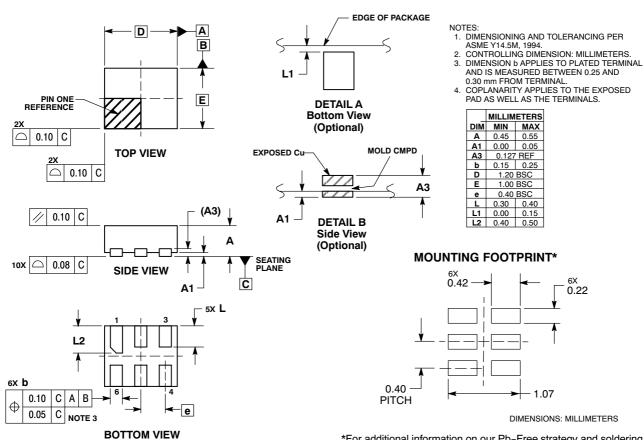
# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NLU1GT125MUTCG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NLU1GT125AMX1TCG	ULLGA6, 1.45 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel
NLU1GT125BMX1TCG	ULLGA6, 1.2 x 1.0, 0.4P (Pb-Free)	3000 / Tape & Reel
NLU1GT125CMX1TCG	ULLGA6, 1.0 x 1.0, 0.35P (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

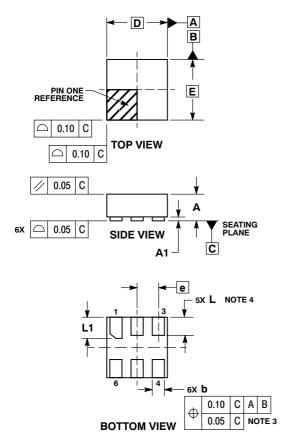
# PACKAGE DIMENSIONS

UDFN6, 1.2x1.0, 0.4P CASE 517AA-01 ISSUE C



# **PACKAGE DIMENSIONS**

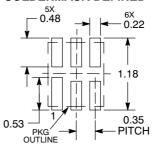
ULLGA6 1.0x1.0, 0.35P CASE 613AD-01 ISSUE A



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
  4. A MAXIMUM OF 0.05 PULL BACK OF THE PLATED TERMINAL FROM THE EDGE OF THE PACKAGE IS ALLOWED. PACKAGE IS ALLOWED.

	MILLIMETERS					
DIM	MIN	MAX				
Α	-	0.40				
A1	0.00	0.05				
b	0.12	0.22				
D	1.00	BSC				
E	1.00	BSC				
е	0.35	BSC				
L	0.25	0.35				
L1	0.30	0.40				

# **MOUNTING FOOTPRINT SOLDERMASK DEFINED\***

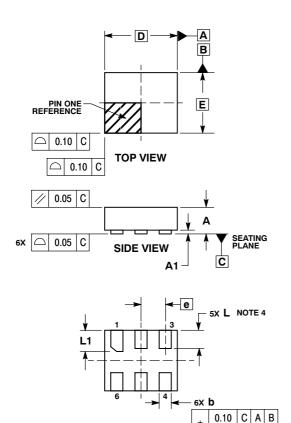


**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# PACKAGE DIMENSIONS

ULLGA6 1.2x1.0, 0.4P CASE 613AE-01 ISSUE A



**BOTTOM VIEW** 

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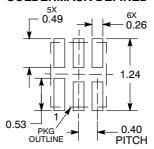
0.05 C NOTE 3

#### NOTES:

- ITES:
  DIMENSIONING AND TOLERANCING PER
  ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSION 6 APPLIES TO PLATED TERMINAL
  AND IS MEASURED BETWEEN 0.15 AND
  0.30 mm FROM THE TERMINAL TIP.
  A MAXIMUM OF 0.05 PULL BACK OF THE
  PLATED TERMINAL FROM THE EDGE OF THE
  PACKAGE IS ALLOWED.

	<b>MILLIMETERS</b>						
DIM	MIN	MAX					
Α		0.40					
A1	0.00	0.05					
b	0.15	0.25					
D	1.20 BSC						
Е	1.00	BSC					
е	0.40 BSC						
L	0.25	0.35					
11	0.35	0.45					

# **MOUNTING FOOTPRINT SOLDERMASK DEFINED\***

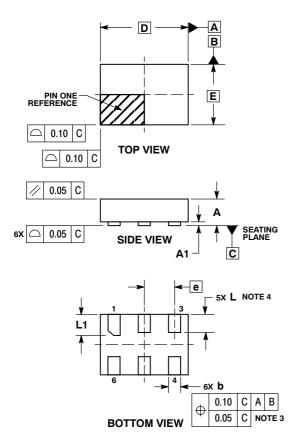


**DIMENSIONS: MILLIMETERS** 

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# PACKAGE DIMENSIONS

ULLGA6 1.45x1.0, 0.5P CASE 613AF-01 **ISSUE A** 

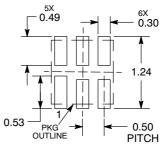


#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.
- A MAXIMUM OF 0.05 PULL BACK OF THE PLATED TERMINAL FROM THE EDGE OF THE PACKAGE IS ALLOWED.

_	MILLIMETERS						
DIM	MIN	MAX					
Α		0.40					
A1	0.00	0.05					
b	0.15	0.25					
D	1.45 BSC						
E	1.00	BSC					
е	0.50	BSC					
L	0.25	0.35					
L1	0.30	0.40					

#### **MOUNTING FOOTPRINT** SOLDERMASK DEFINED\*



**DIMENSIONS: MILLIMETERS** 

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